Yifan (Frank) Zhang

120 Valentine Place 4029, Ithaca, NY, 14850

Tel: (917)-442-8359 E-mail: yz2439@cornell.edu

Cornell University

09/2019-Present

Bachelor of Science in Electrical and Computer Engineering, 2022

- Cumulative GPA: 4.15/4.3; Dean's List
- Rawlings Cornell Presidential Research Scholar
- John G. Pertsch Prize (top two in department)

EDUCATION

• Minor in Physics and Material Science

09/2018-05/2019

Cooper Union for the Advancement of Science and Art

Bachelor of Engineering in Electrical Engineering, 2022

- Cumulative GPA: 3.9; Major GPA 4.0; Dean's List
- Sub-project lead in FSAE project team

Undergraduate Researcher at Jena-Xing Group

09/2019-Present

PI: Prof. Debdeep Jena

• Project 1: Tight-binding model for ultra-wide bandgap semiconductors

Derived the first tight-binding model of α - and β - Ga_2O_3 and Al_2O_3 . The model well captures the key features of the electronic band structure with a minimum computational cost. There are two sets of models with two basis wavefunctions:

- o atomic orbitals semi-empirically fitted to density functional theory (DFT) bandstructure
- o maximally-localized Wannier functions derived directly from DFT. Constraints and simplifications based on symmetry and orbital nature are used to disentangle unnecessary features in the complicated electronic structures.

This model enables the study of large-scale bulk materials, devices, and heterostructures with full electronic structure.

• Project 2: Nitride superconductivity, integration, and devices

RESEARCH EXPERIENCE Studied superconductor NbN epitaxially integrated with nitride semiconductors. Aim to fabricate devices advantageous from high crystal quality and epitaxial interfaces.

- Participated in the process development and characterization of NbN/AlN/NbN Josephson junction. Investigated and solved etch issue related to surface organic contaminant. Currently characterizing the device and improving the contact.
- Characterized the exotic transport features of NbN nanowire near critical temperature.
 Identified signatures of Kosterlitz-Thouless transition, discretized phase-slip centers,
 and thermal-dependent current retrapping dynamics.
- Studied NbN/AlN/NbN Josephson junction with tunneling model and Hubbard model under Bogoliubov-de Genne formalism. Predicted the ideal/non-ideal behavior as well as microscopic features

• Project 3: High-field transport simulation in AlN

- Simulated the electron transport in AlN at high-field using monte-carlo method. Currently looking for impact ionization, its anisotropy, and anomalous temperature dependence due to the bandstructure effect. Such effect is unseen in narrow-bandgap semiconductors and hasn't been fully studied to date.
- Will also study AlGaN alloy at different compositions.

brication	
ductor, RF System, Piezoelectric System,	
SP, Probability	
es,	
odynamics	
New York, NY	
6/2019 – 08/2019	
tself under urban sensory system.	
m under ROS.	
Shenzhen, China	
7/2018 – 08/2018	
and YAGEO.	
stem (MPS).	
nd Al ₂ O ₃ . J. Appl.	
west Ultra Wide-	
ce.	
ium Lead Halide	
sign, 18(6), 3458-	
, (-),	
el,	